

ZERO BIAS SCHOTTKY DIODE

DESCRIPTION:

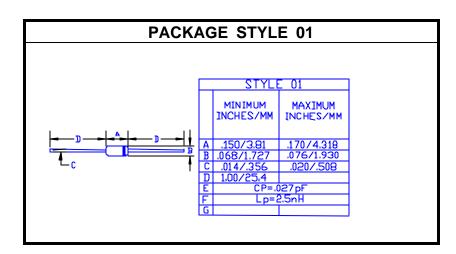
The **HSCH-3486** is a Silicon Zero Bias Schottky Barrier Diode Designed for High Sensitivity Detector and Low Starved Mixer Applications up to 10 GHz.

FEATURES INCXLUDE:

- Replacement for HSCH3486 and MA4E928B-54
- True Zero Bias Operation
- Hermetic Glass Package

MAXIMUM RATINGS

١ _F	10 mA				
V _R	2.0 V				
P _{DISS}	$300 \text{ mW} @ \text{T}_{\text{C}} = 25 \ ^{\text{O}}\text{C}$				
ΤJ	-65 ^o C to +150 ^o C				
T _{STG}	-65 ^o C to +150 ^o C				
T _{SOLD}	+230 ^O C for 5 seconds				



CHARACTERISTICS $T_c = 25 °C$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
V _F	l _F = 1.0 mA				225	mV
C _T	V _R = 0 V	f = 1.0 MHz			0.5	pF
T _{ss}	B _W = 2.0 MHz	f = 10 GHz			-54	dBm
γ	P _{IN} = -40 dBm	f = 10 GHz	7.5			mV/μW
Rv	P _{IN} = -40 dBm	f = 10 GHz	2		8	K ohms

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